

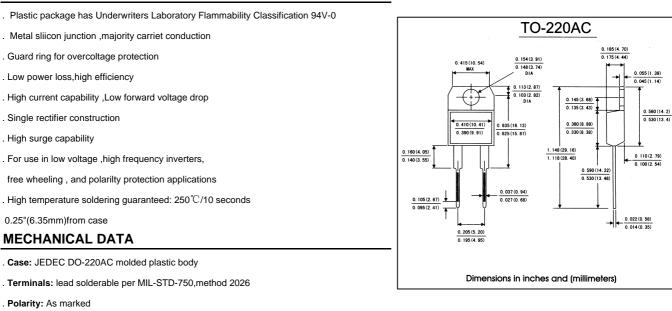
SR820 THRU SR8A0(SINGLE CHIP)

SCHOTTKY BARRIER RECTIFIER

Reverse Voltage - 20 to 100 Volts

Forward Current - 8.0Amperes

FEATURES



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

(Ratings at 25 $^\circ\!C$ ambient temperature unless otherwise specified,Single phase,half wave,resistive or inductive)

load. For capacitive load, derate by 20%)

. Mounting Position: Any . Weight: 0.08 ounce, 2.24 gram

		Symbols	SR820	SR830	SR840	SR850	SR860	SR880	SR8A0	Units
Maximum repetitive peak reverse voltage		Vrrm	20	30	40	50	60	80	100	Volts
Maximum RMS voltage		Vrms	14	21	28	35	42	57	71	Volts
Maximum DC blocking voltage		VDC	20	30	40	50	60	80	100	Volts
Macimum average forward rectified current(see Fig.1)		l(AV)	8.0							Amps
Repetitive peak forward current(square wavr, 20KHz) at Tc=105 °C		Ifrm	16.0						Amps	
Peak forward surge current 8.3ms singel half sine-wave superimposed on rated load (JEDEC method)		IFSM	150.0						Amps	
Maximum instantaneous forward voltage at 7.5 A(Note 1)		VF		0.65 0.75 0.8 0.85			0.85	Volts		
Maximum instantaneous reverse	TA=25℃	IR	1.0							mA
current at rated DC blocking voltage(Note 1)	TA=125℃	IR		15	15 50					ma
Typeical thermal resistance(Note 2)		R θ_{JC}	2.5						°C/W	
Operating junction temperature range		TJ		-65 to +150 -65 to +150						°C
storage temperature range		Тѕтс	-65 to +150						°C	

Notes: 1. Pulse test: 300 μ s pulse width,1% duty cycle

2. Thermal resistance from juntion to case



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RATINGS AND CHARACTERISTIC CURVES SR820 THRU SR8A0(SINGLE CHIP)

FLG.1-FORWARD CURRENT DERATING CURVE

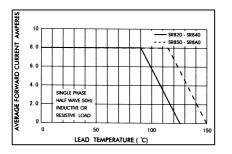


FIG.2-TYPICAL INSTANTANEOUS FORWARD

CHARACTERISTICS

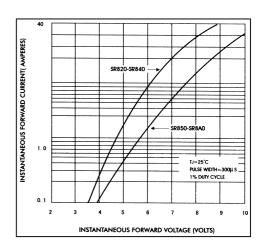


FIG.4-TYPICAL JUNCTION CAPACITANCE

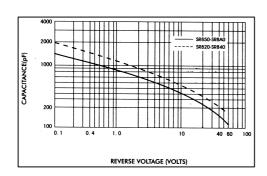


FIG.5-MAXIMUM NON-REPETITIVE PEAK

FORWARD SURGE CURRENT

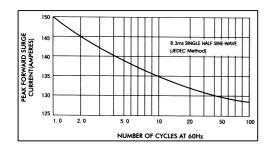


FIG.3-TYPICAL REVERSE CHARACTERISTICS

